



N-Channel Power MOSFET

600V, 13A, 0.26Ω

FEATURES

- Super-Junction technology
- High performance, small R_{DS(ON)}*Q_g figure of merit (FOM)
- High ruggedness performance
- 100% UIS tested
- High commutation performance
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS			
PARAMETER VALUE UNIT			
V _{DS}	600	V	
R _{DS(on)} (max)	0.26	Ω	
Q_g	30	nC	



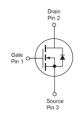




APPLICATION

- Power Supply
- AC/DC LED Lighting





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	600	V	
Gate-Source Voltage		V _{GS}	±30	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	1	13	Α	
	$T_C = 100$ °C	I _D	7.8	А	
Pulsed Drain Current (Note 2)		I _{DM}	39	Α	
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	32.1	W	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	196.9	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	2.5	Α	
Operating Junction and Storage Tem	perature Range	T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	R _{eJC}	3.9	°C/W
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.

1





ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.0	3.0	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 3.9A$	R _{DS(on)}		0.19	0.26	Ω
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 380V, I_{D} = 13A,$ $V_{GS} = 10V$	Qg		30		nC
Gate-Source Charge		Q_{gs}		6.6		
Gate-Drain Charge		Q_{gd}		11.7		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		1273		_
Output Capacitance	f = 1.0MHz	C _{oss}		92		pF
Gate Resistance	F = 1MHz, open drain	R_g		3.1		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 13A, V_{GS} = 10V,$	t _{d(on)}		28.4		
Turn-On Rise Time		t _r		13.2		
Turn-Off Delay Time		t _{d(off)}		90.8		ns
Turn-Off Fall Time	I _D = 13A, v _{GS} = 10v,	t _f		10		
Source-Drain Diode (Note 4)		•		•		
Forward On Voltage	I _S = 13A, V _{GS} = 0V	V _{SD}			1.4	V
Reverse Recovery Time	V _R =100V, I _S = 13A	t _{rr}		346.6		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		4.2		μC

2

Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L=63mH, $I_{AS}=2.5A$, $V_{DD}=50V$, $R_{G}=25\Omega$, Starting $T_{J}=25^{\circ}C$
- 4. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.



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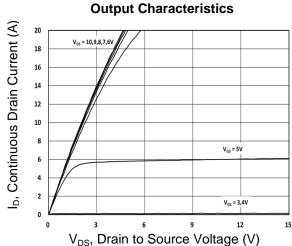
ORDERING INFORMATION

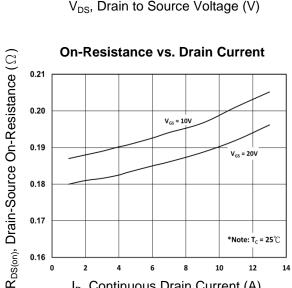
PART NO.	PACKAGE	PACKING
TSM60NB260CI C0G	ITO-220	50pcs / Tube



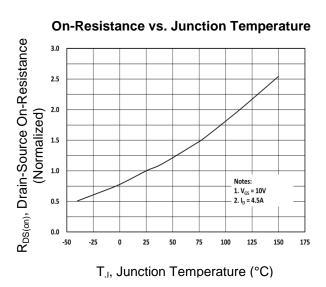
CHARACTERISTICS CURVES

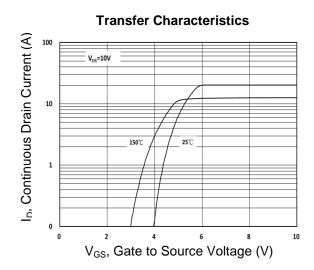
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

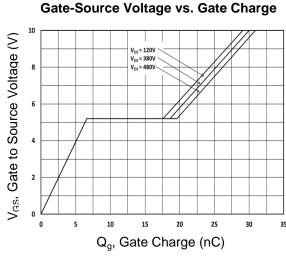


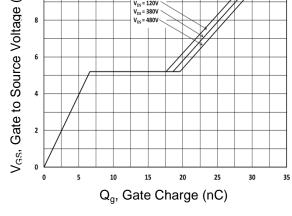


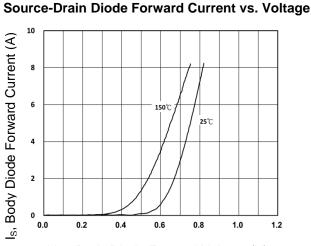
ID, Continuous Drain Current (A)











V_{SD}, Body Diode Forward Voltage (V)

Version: A1511

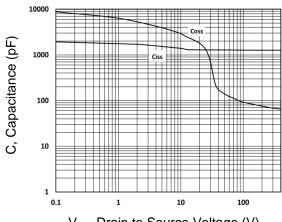
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CHARACTERISTICS CURVES

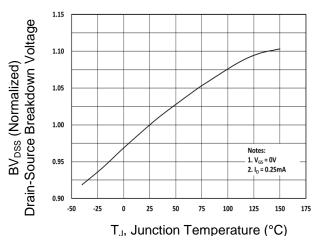
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Capacitance vs. Drain-Source Voltage

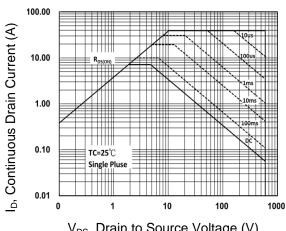


V_{DS}, Drain to Source Voltage (V)

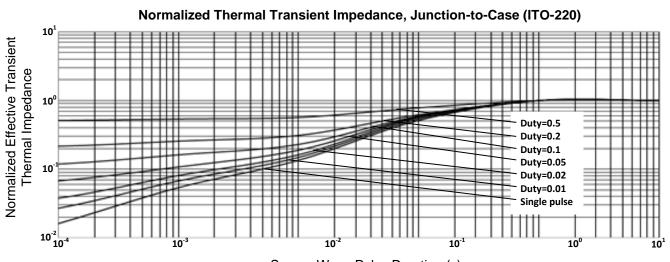
BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area (ITO-220)



V_{DS}, Drain to Source Voltage (V)



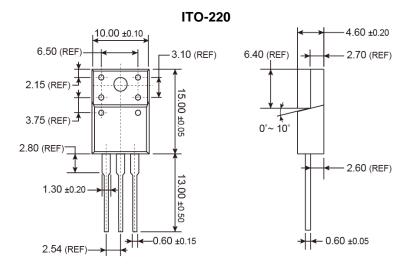
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Square Wave Pulse Duration (s)





PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



6

MARKING DIAGRAM



G = Halogen Free

Y = Year Code

WW = Week Code (01~52)

F = Factory Code



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